



# 9/c.  
3/4/03  
PATENT Mullish  
81738.0292

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

KOJIMA, et al.

Serial No: 09/803,624

Filed: March 9, 2001

For: SMALL GEOMETRY HIGH  
VOLTAGE SEMICONDUCTOR  
DEVICE

AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Office Action dated August 13, 2002, the period for response having been extended to February 13, 2003 by the accompanying Petition For Extension Of Time, please amend the above-identified application as follows. A marked-up copy, showing the changes made thereto, is appended.

IN THE CLAIMS:

Please amend Claim 28 and add new claims 30 to 35 as follows. A marked up copy of the amended claim, showing the changes made thereto, is attached. The claims, as pending in the present application, are as follows:

27. (Not Changed From Previous Version) A semiconductor integrated circuit according to claim 28, wherein the minimum gate length in the channel length direction of the LVMISFET is in the range of 1.5 – 2.5  $\mu$ m.

*C1*  
28. (Twice Amended) A semiconductor integrated circuit comprising:  
an HVMISFET (high withstand voltage MOSFET) having:

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